Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSIV)

2SJ304

DC-DC Converter, Relay Drive and Motor Drive Applications

• 4-V gate drive

• Low drain-source ON resistance : $RDS (ON) = 80 \text{ m}\Omega \text{ (typ.)}$ • High forward transfer admittance : $|Y_{fs}| = 8.0 \text{ S (typ.)}$

• Low leakage current : IDSS = $-100 \mu A \text{ (max)} \text{ (VDS} = -60 V)$

• Enhancement mode : $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	-60	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-14	Α	
	Pulse(Note 1)	I_{DP}	-56	A 	
Drain power dissipation (Tc = 25°C)		P_{D}	40	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device.

Please handle with caution.



Electrical Characteristics (Ta = 25°C)

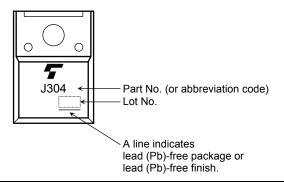
Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μA
Drain cut-off cur	rrent	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	_	_	-100	μA
Drain-source br	eakdown	V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-60	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8	_	-2.0	V
David Colored	D	V _{GS} = -4 V, I _D = -5 A	-	130	190	- mΩ	
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = -10 V, I _D = -7 A	_	80		120
Forward transfer	admittance	Y _{fs}	V _{DS} = -10 V, I _D = -7 A	5.0	8.0	_	S
Input capacitano	е	C _{iss}		_	1200	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	220	_	pF
Output capacitance		Coss		_	550	_	
Switching time	Rise time	t _r	$\begin{array}{c c} V_{GS} & 0V & & I_{D} = -7A \\ \hline V_{GS} & 0V & & & \\ \hline -10V & & & \\ \hline & & \\ \hline & & & \\ \hline & & \\ \hline & & \\ \hline & & \\ \hline & & & \\ \hline & $	_	20	_	
	Turn-on time	t _{on}		ı	30	_	ns
	Fall time	t _f		ı	25	_	- 113
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$		100	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	45	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx -48 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -14 \text{ A}$		30	_	nC
Gate-drain ("miller") charge		Q _{gd}			15	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

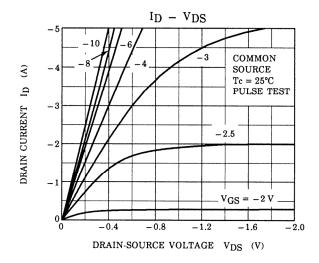
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	-14	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	-	_	-56	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = -14 A, V _{GS} = 0 V	_	_	1.7	V
Reverse recovery time	t _{rr}	I _{DR} = -14 A, V _{GS} = 0 V	_	110	_	ns
Reverse recovery charge	Q _{rr}	dI_{DR} / $dt = 50 \text{ A}$ / μs	_	0.18	_	μC

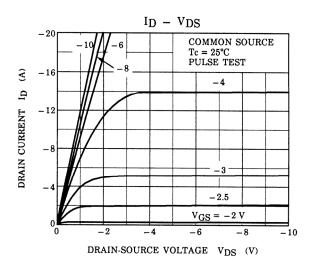
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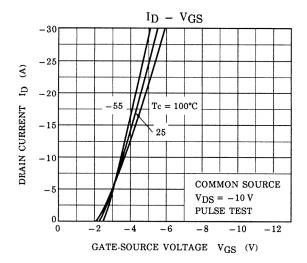
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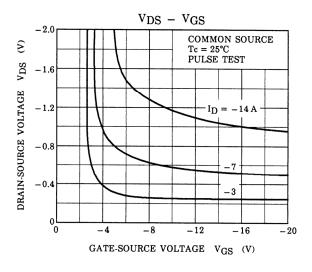


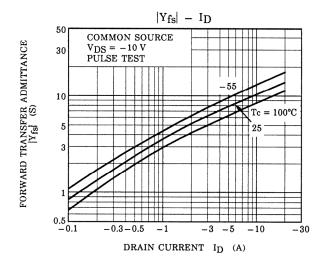
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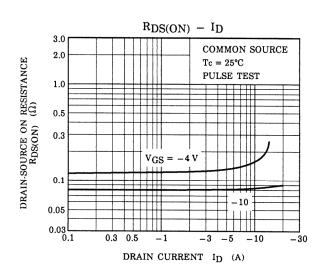


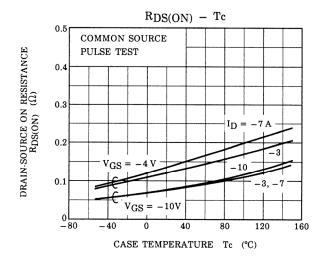


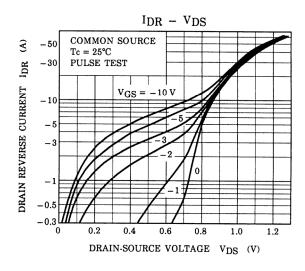


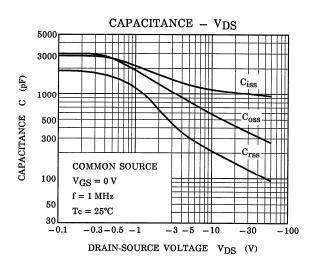


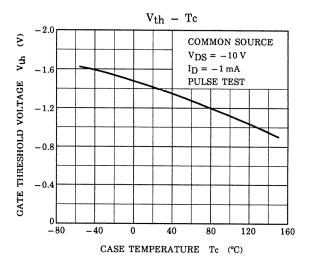


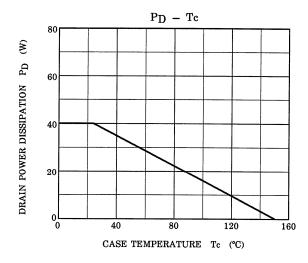


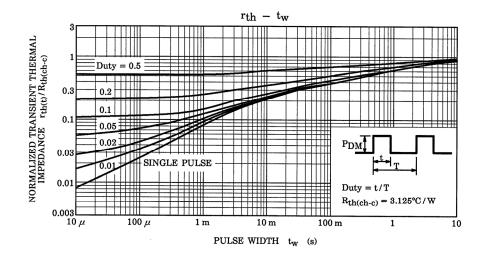


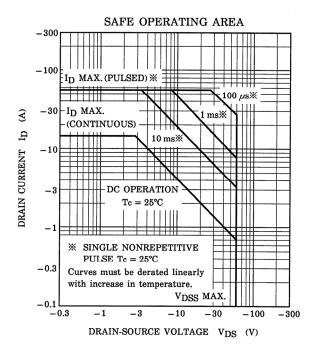












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